

MOSFET

StrongIRFET™2 Power-Transistor, 60 V

Features

- Optimized for wide range of applications
- N-channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

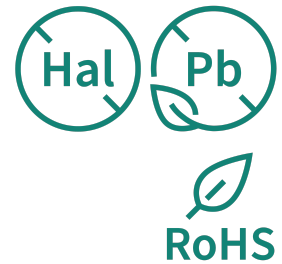
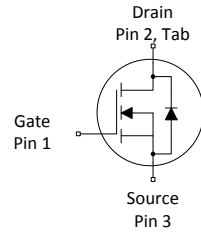
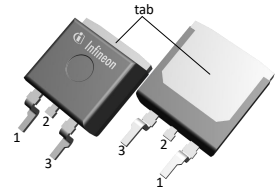
Product validation

Qualified according to JEDEC Standard

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),max}$	2.9	mΩ
I_D	120	A
Q_{oss}	68	nC
$Q_G(0V..10V)$	68	nC

D²PAK



Type / Ordering code	Package	Marking	Related links
IPB029N06NF2S	PG-TO263-3	029N06NS	-



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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	120 93 26	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	480	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	192	mJ	$I_D=70\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	158 3.8	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=40\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.95	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	40	°C/W	
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.1	2.8	3.3	V	$V_{DS}=V_{GS}$, $I_D=80\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.5 10	1 100	μA	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.4 3.0	2.9 4.2	m Ω	$V_{GS}=10\text{ V}$, $I_D=70\text{ A}$ $V_{GS}=6\text{ V}$, $I_D=35\text{ A}$
Gate resistance	R_G	-	3.2	-	Ω	-
Transconductance ⁶⁾	g_{fs}	70	-	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=70\text{ A}$

⁶⁾ Defined by design. Not subject to production test.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4600	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	1000	-	pF	
Reverse transfer capacitance	C_{rss}	-	51	-	pF	
Turn-on delay time	$t_{d(on)}$	-	17	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=70\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	31	-	ns	
Turn-off delay time	$t_{d(off)}$	-	33	-	ns	
Fall time	t_f	-	14	-	ns	

Table 6 Gate charge characteristics ⁷⁾

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	21	-	nC	$V_{DD}=30\text{ V}$, $I_D=70\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	13	-	nC	
Gate to drain charge	Q_{gd}	-	13	-	nC	
Switching charge	Q_{sw}	-	21	-	nC	
Gate charge total ⁸⁾	Q_g	-	68	102	nC	
Gate plateau voltage	$V_{plateau}$	-	4.6	-	V	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	63	-	nC	
Output charge	Q_{oss}	-	68	-	nC	

7) See "Gate charge waveforms" for parameter definition

8) Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	96	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	480	A	
Diode forward voltage	V_{SD}	-	0.91	1.1	V	$V_{GS}=0\text{ V}, I_F=70\text{ A}, T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	41	-	ns	$V_R=30\text{ V}, I_F=70\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	44	-	nC	
Reverse recovery time	t_{rr}	-	28	-	ns	$V_R=30\text{ V}, I_F=70\text{ A}, di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	120	-	nC	

4 Electrical characteristics diagrams

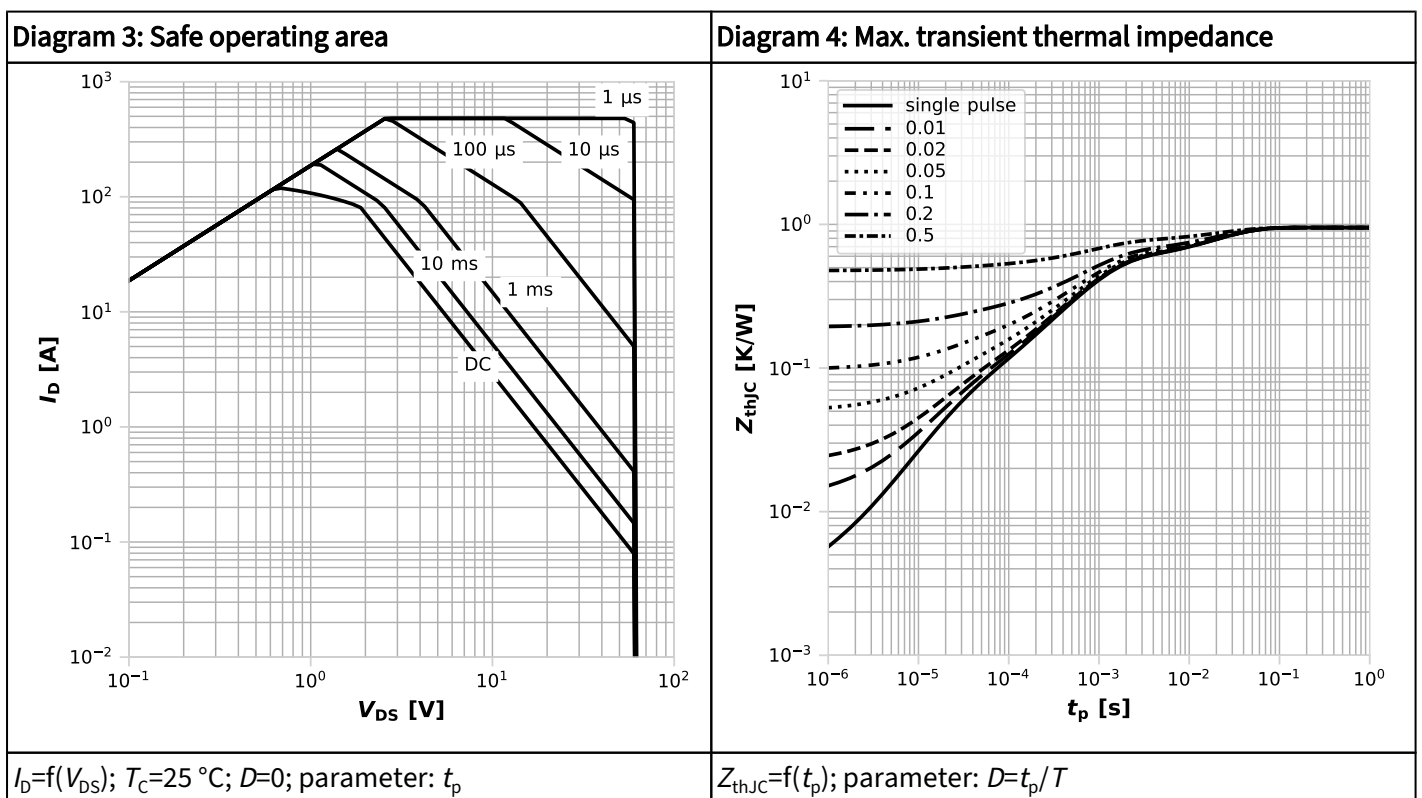
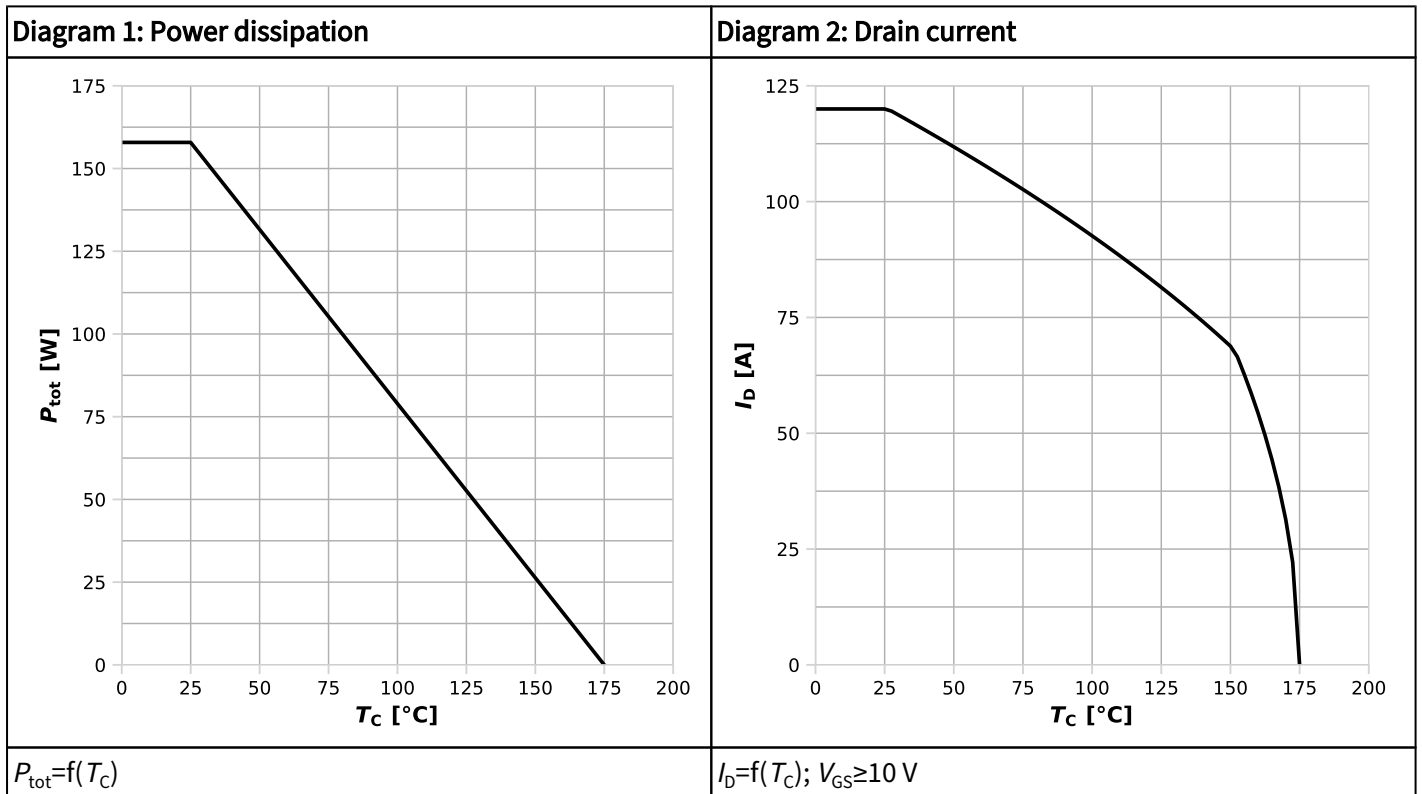
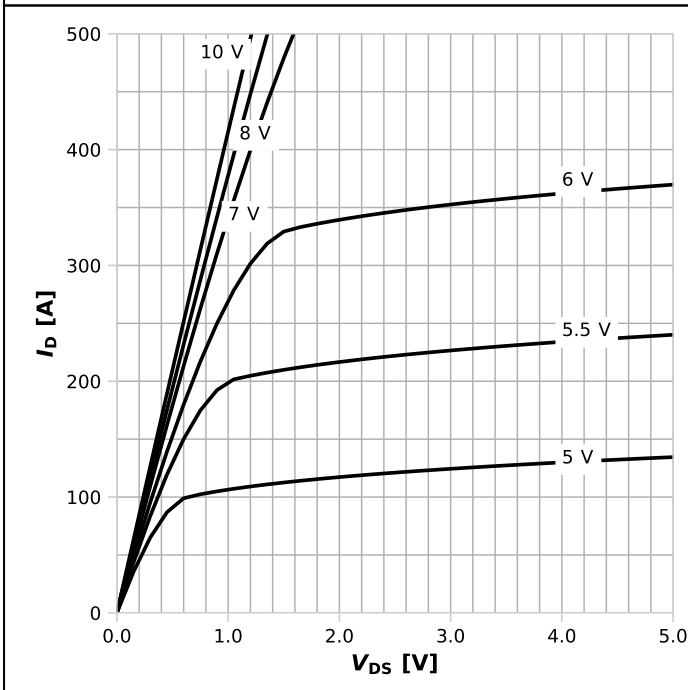
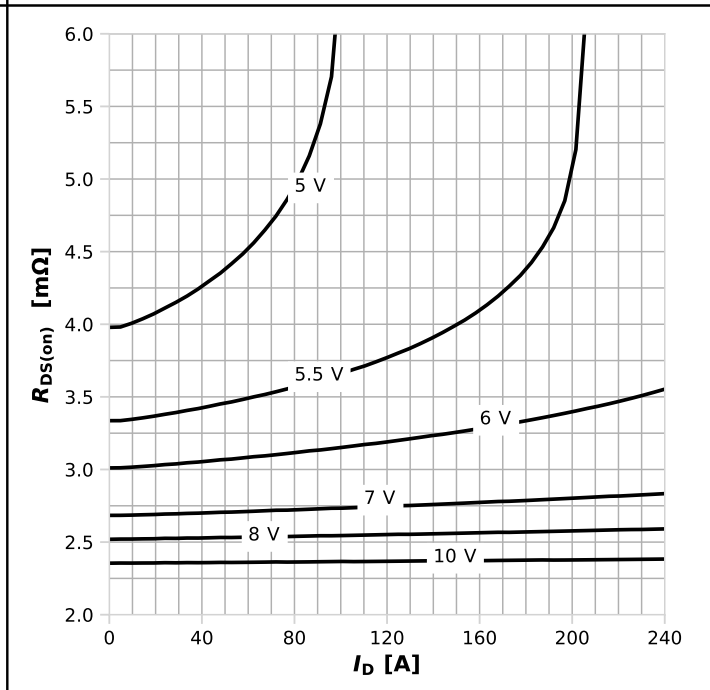


Diagram 5: Typ. output characteristics



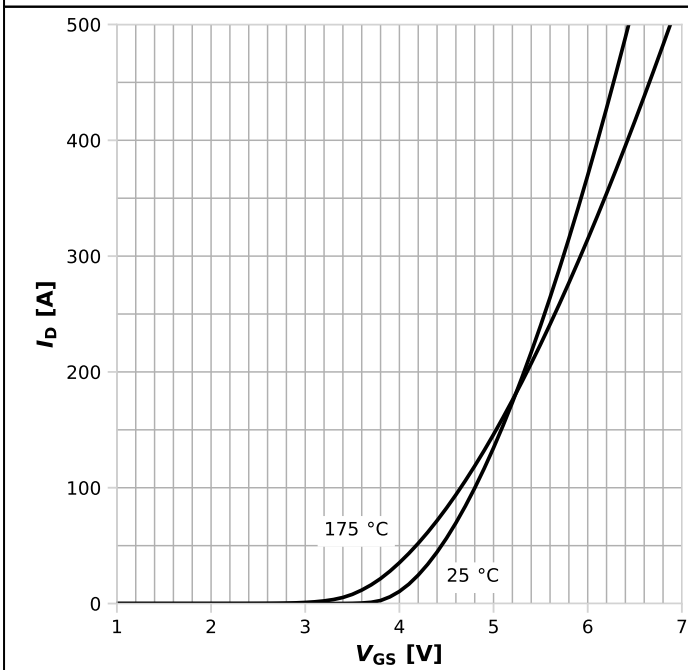
$I_D = f(V_{DS}), T_j = 25\text{ °C};$ parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



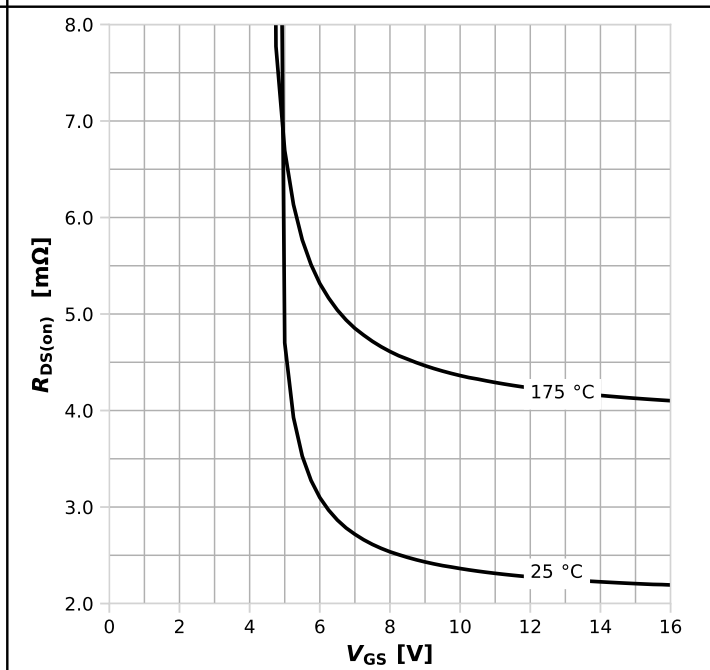
$R_{DS(on)} = f(I_D), T_j = 25\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



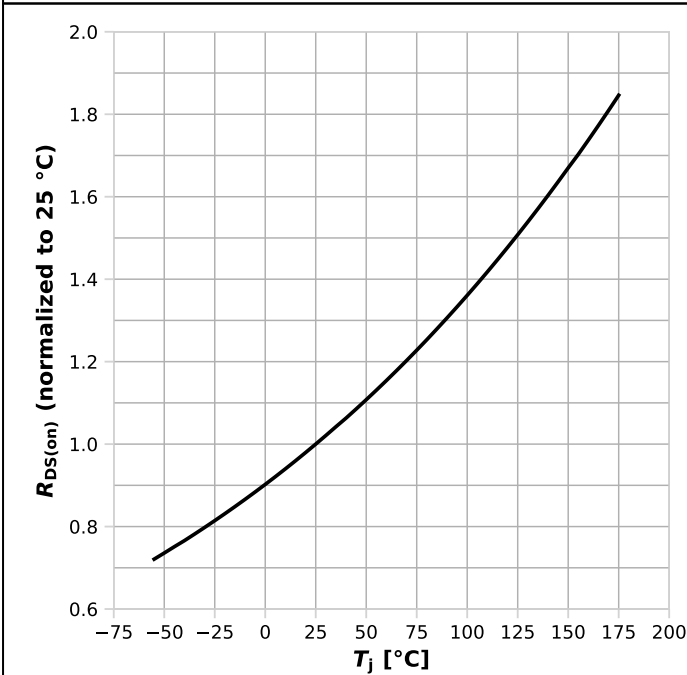
$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max};$ parameter: T_j

Diagram 8: Typ. drain-source on resistance



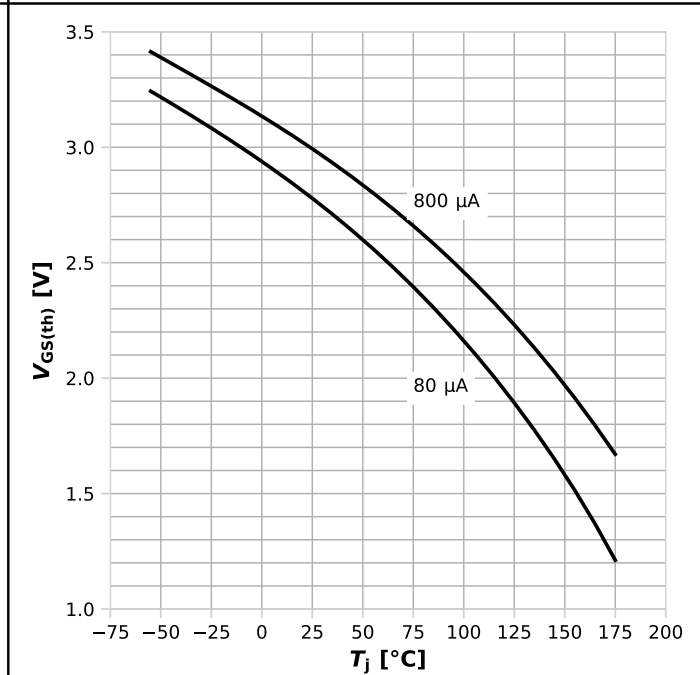
$R_{DS(on)} = f(V_{GS}), I_D = 70\text{ A};$ parameter: T_j

Diagram 9: Normalized drain-source on resistance



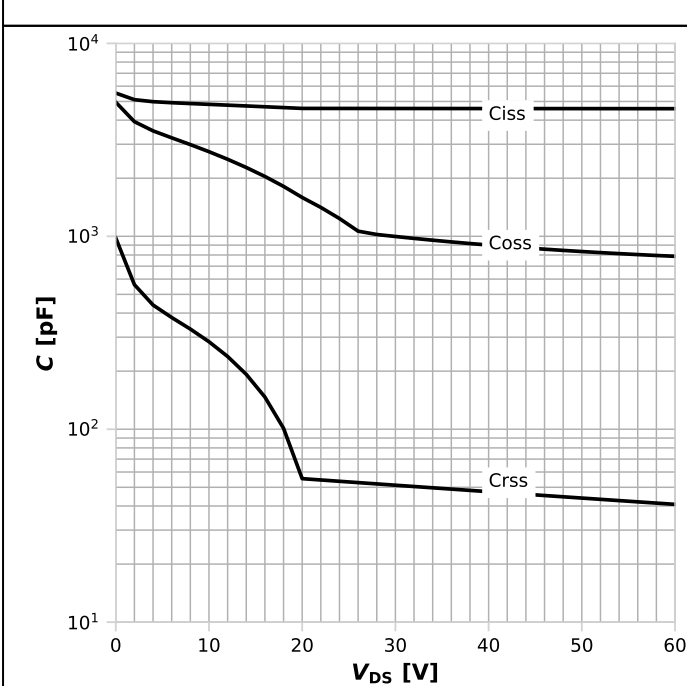
$$R_{DS(on)} = f(T_j), I_D = 70 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



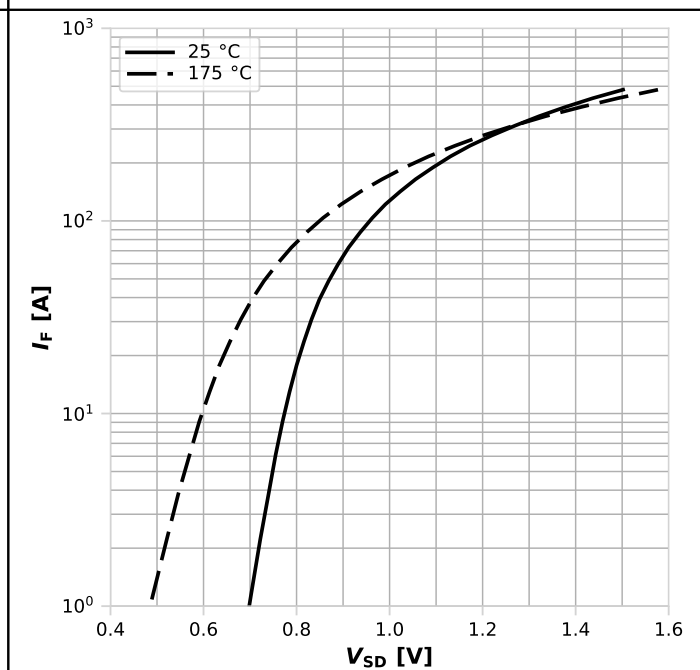
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_b$$

Diagram 11: Typ. capacitances



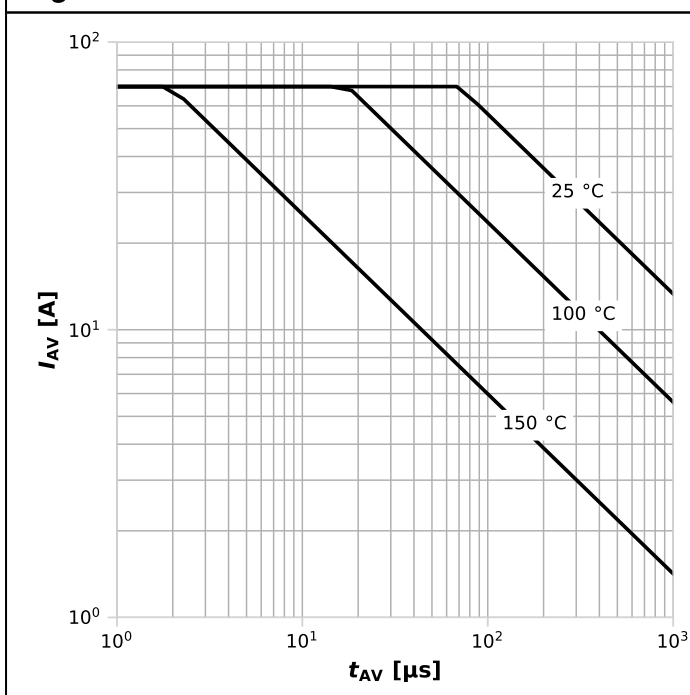
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Typ. forward characteristics of reverse diode



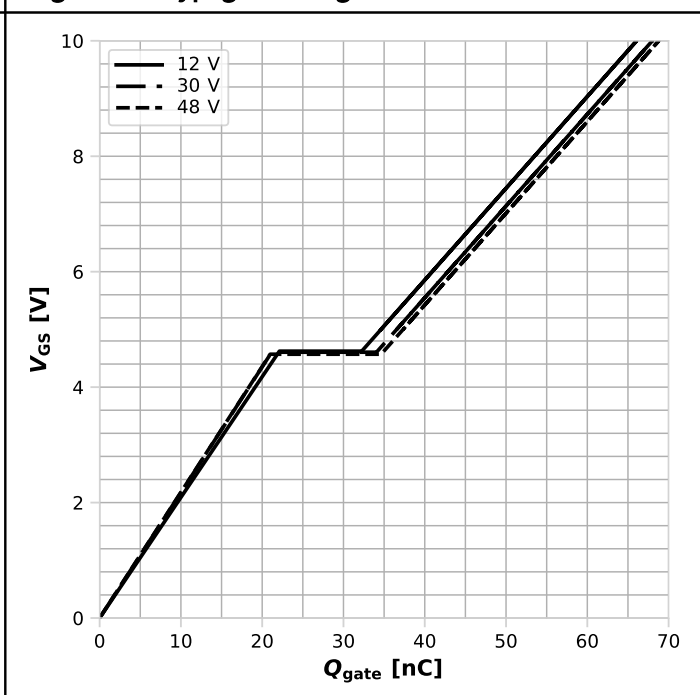
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



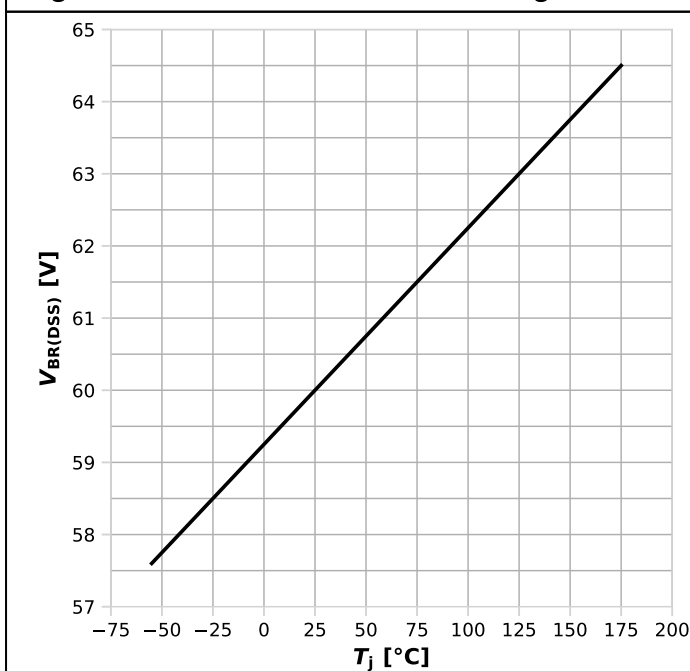
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



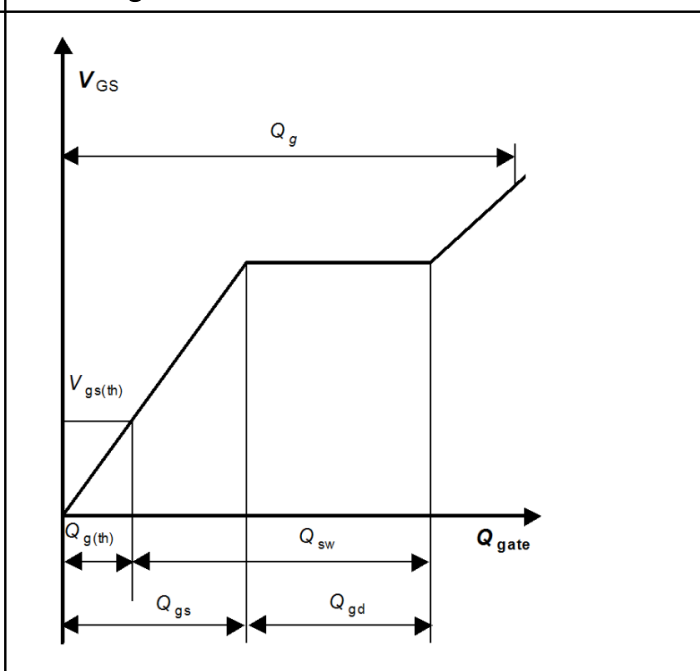
$V_{GS}=f(Q_{gate}), I_D=70 \text{ A pulsed}, T_j=25 \text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



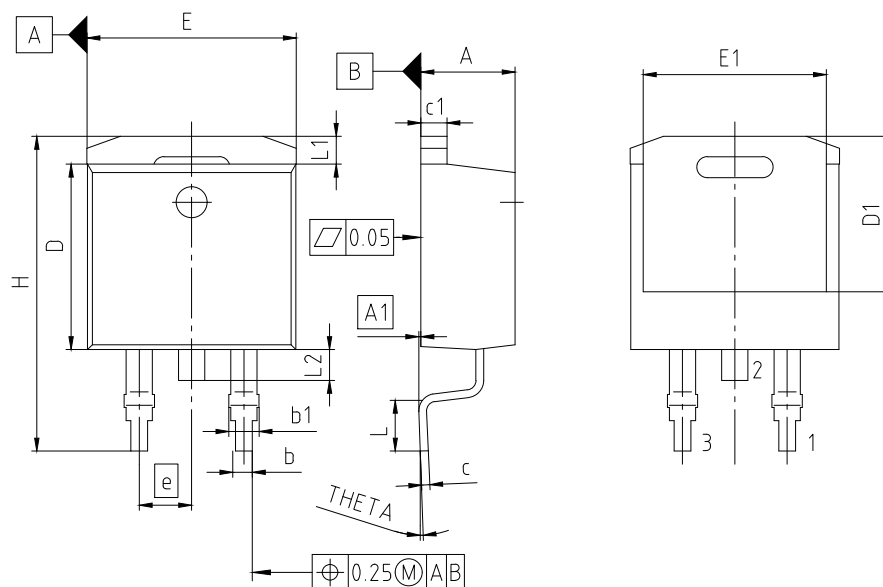
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Gate charge waveforms



-

5 Package outlines



PACKAGE - GROUP NUMBER: PG-T0263-3-U02		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.06	4.83
A1	0.00	0.25
b	0.51	1.00
b1	1.07	1.78
c	0.30	0.73
c1	1.14	1.65
D	8.38	9.65
D1	6.60	7.50
E	9.65	10.67
E1	6.22	8.70
e	2.54	
N	3	
H	14.60	15.88
L	1.52	2.60
L1	1.05	1.68
L2	1.35	1.78
THETA	-9.00°	8.00°

PG-T0263-3-10: OPTIONAL

5:1

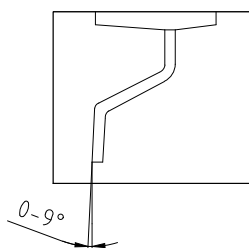


Figure 1 Outline PG-T0263-3, dimensions in mm

Revision history

IPB029N06NF2S

Revision 2024-10-16, Rev. 2.1

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2022-10-19	Release of final version
2.1	2024-10-16	Added trr and Qrr at diF/dt=100 A/μs

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